2SC3835

Silicon NPN Triple Diffused Planar Transistor (Switching Transistor)

Application: Humidifier, DC-DC Converter, and General Purpose

	Absolute	(Ta=25°C)	
	Symbol	2SC3835		Unit
	Vсво	200		V
	VCEO	120		V
	VEBO	8		V
	Ic	7(Pulse14)		А
	Ів	3		А
	Pc	70(Tc=25°C)		W

-55 to +150

Τj Tstg

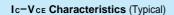
Electrical CI	naracteristics	(Ta=25°C)			
Symbol	Conditions	2SC3835	Unit		
Ісво	Vcb=200V	100max	μΑ		
lebo	VEB=8V	100max	μΑ		
V(BR)CEO	Ic=50mA	120min	V		
hfe	Vce=4V, Ic=3A	70 to 220			
VcE(sat)	Ic=3A, IB=0.3A	0.5max	V		
VBE(sat)	Ic=3A, IB=0.3A	1.2max	V		
fт	Vce=12V, Ie=-0.5A	30typ	MHz		
Сов	Vcb=10V, f=1MHz	110typ	рF		

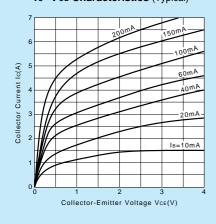
Weight: Approx 6.0g a. Type No. b. Lot No.

External Dimensions MT-100(TO3P)

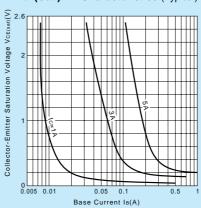
Typical Switching Characteristics (Common Emitter)

- 1) 1 1												
Vcc (V)	RL (Ω)	Ic (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (A)	IB2 (A)	ton (µs)	tstg (µs)	tf (µs)			
50	16.7	3	10	-5	0.3	-0.6	0.5max	3.0max	0.5max			

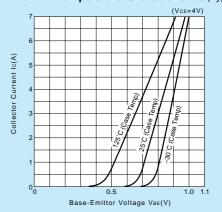




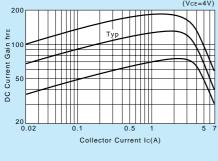
VcE(sat)-IB Characteristics (Typical)



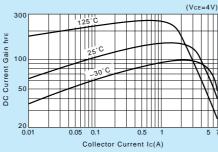
Ic-VBE Temperature Characteristics (Typical)



hfe-Ic Characteristics (Typical)



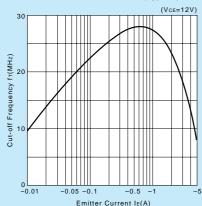
hfe-Ic Temperature Characteristics (Typical)



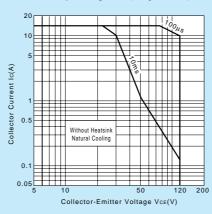
 $\theta_{\text{j-a}}\text{--t Characteristics}$



fT-IE Characteristics (Typical)



Safe Operating Area (Single Pulse)



Pc-Ta Derating

